# **Quad Bus Buffer**

# with 3-State Control Inputs

The MC74VHC125 is a high speed CMOS quad bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC125 requires the 3–state control input ( $\overline{OE}$ ) to be set High to place the output into the high impedance state.

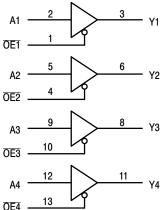
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

#### **Features**

- High Speed:  $t_{PD} = 3.8 \text{ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **LOGIC DIAGRAM**

#### **Active-Low Output Enables**



#### **FUNCTION TABLE**

VHC125					
outs	Output				
ΟE	Υ				
L	Н				
L	L				
Н	Z				
	OE L L				



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14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G

# PIN CONNECTION AND MARKING DIAGRAM

(Top View)

OE1 [	1 ●	14	] v <sub>cc</sub>
A1 [	2	13	] OE4
Y1 [	3	12	] A4
OE2	4	11	] Y4
A2 [	5	10	OE3
Y2 [	6	9	] A3
GND [	7	8	] Y3
	· ·		•

#### **DEVICE MARKING INFORMATION**

See general marking information in the device marking section on page 6 of this data sheet.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>out</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current	- 20	mA
I <sub>OK</sub>	Output Diode Current	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating – SÓIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $ \begin{array}{c} V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V} \end{array} $	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHC125DG	SOIC-14 (Pb-Free)	55 Units / Rail
NLV74VHC125DG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC74VHC125DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NLV74VHC125DR2G*	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHC125DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV74VHC125DTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	1	Γ <sub>A</sub> = 25°(	;	<b>T</b> <sub>A</sub> ≤	85°C	<b>T</b> <sub>A</sub> ≤ '	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50  \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum Low–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			± 0.2 5		± 2.5		± 2.5	μΑ
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5V or GND	0 to 5.5			± 0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40		40	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

				т	<sub>A</sub> = 25°	С	T <sub>A</sub> = 5	≤ 85°C		= ≤ 5°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3V$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0	1.0 1.0	12.0 16.0	ns
		$V_{CC} = 5.0 \pm 0.5V$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	8.5 10.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable TIme, OE to Y	$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0	1.0 1.0	11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1 \text{ k}\Omega$			3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0	1.0 1.0	7.5 9.5	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output Disable Time, OE to Y	$\begin{aligned} &V_{CC} = 3.3 \pm 0.3V \\ &R_L = 1 \; k\Omega \end{aligned}$	C <sub>L</sub> = 50 pF		9.5	13.2	1.0	15.0	1.0	18.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		6.1	8.8	1.0	10.0	1.0	12.0	
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output-to-Output Skew	V <sub>CC</sub> = 3.3 ± 0.3V (Note 1)	C <sub>L</sub> = 50 pF			1.5		1.5		1.5	ns
		$V_{CC} = 5.0 \pm 0.5V$ (Note 1)	C <sub>L</sub> = 50 pF			1.0		1.0		1.0	
C <sub>in</sub>	Maximum Input Capacitance				4	10		10		10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High Impedance State)				6						pF

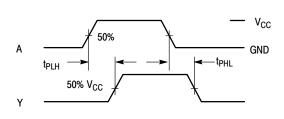
ĺ			Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
	$C_{PD}$	Power Dissipation Capacitance (Note 2)	14	pF

## **NOISE CHARACTERISTICS** (Input $t_{r} = t_{f} = 3.0$ ns, $C_{L} = 50$ pF, $V_{CC} = 5.0$ V)

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per buffer). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

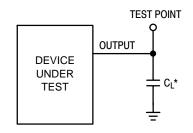
#### **SWITCHING WAVEFORMS**



 $V_{\text{CC}}$ ΟE 50% GND  $t_{PZL}$  $t_{PLZ}$ HIGH **IMPEDANCE** 50% V<sub>CC</sub> Υ  $V_{OL} + 0.3V$  $t_{PZH}$  $t_{PHZ}$ V<sub>OH</sub> - 0.3V 50% V<sub>CC</sub> HIGH **IMPEDANCE** 

Figure 1.

Figure 2.



\*Includes all probe and jig capacitance

DEVICE UNDER TEST  $\begin{array}{c} \text{OUTPUT} & \text{1 k}\Omega \\ \text{OUTPUT} & \text{1 k}\Omega \\ \text{C}_L^* & \text{CONNECT TO V}_{CC} \text{ WHEN TESTING t}_{PLZ} \text{ AND t}_{PZL.} \\ \text{CONNECT TO GND WHEN TESTING t}_{PHZ} \text{ AND t}_{PZH.} \\ \end{array}$ 

TEST POINT

\*Includes all probe and jig capacitance

Figure 3. Test Circuit

Figure 4. Test Circuit

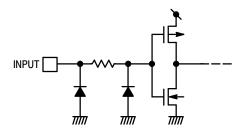
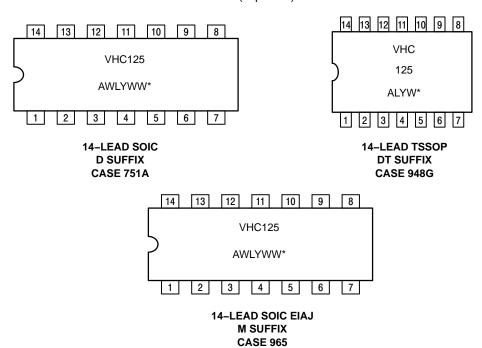


Figure 5. Input Equivalent Circuit

#### **MARKING DIAGRAMS**

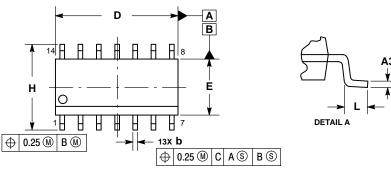
(Top View)

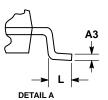


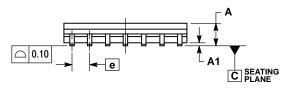
<sup>\*</sup>See Applications Note AND8004/D for date code and traceability information.

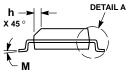
#### **PACKAGE DIMENSIONS**

SOIC-14 CASE 751A-03 ISSUE L









- IOTES:

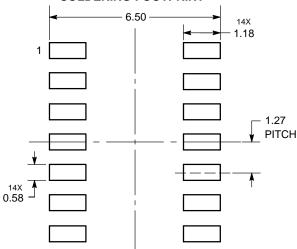
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.

  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

  5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

#### **SOLDERING FOOTPRINT\***

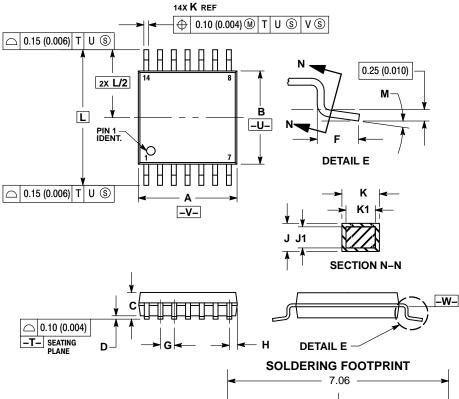


**DIMENSIONS: MILLIMETERS** 

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **PACKAGE DIMENSIONS**

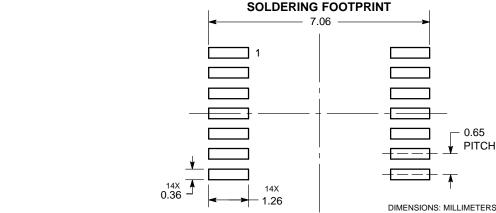
#### TSSOP-14 CASE 948G ISSUE C



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
  MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE
- 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С	-	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
М	0 °	8 °	0°	8 °	



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